New Product



VS-HFA30TA60CHN3

Vishay Semiconductors

RoHS

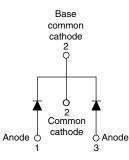
COMPLIANT

HALOGEN

FREE

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 15 A





PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 15 A				
V _R	600 V				
V _F at I _F	1.7 V				
t _{rr} typ.	19 ns				
T _J max.	150 °C				
Diode variation	Common cathode				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA30TA60CHN3 is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A per leg continuous current, the VS-HFA30TA60CHN3 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30TA60CHN3 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		600	V		
Maximum continuous forward current	1	T _C = 100 °C	15			
per device	IF	$1_{\rm C} = 100$ C	30	А		
Single pulse forward current	I _{FSM}		150	A		
Maximum repetitive forward current	I _{FRM}		60			
Maximum power dissignation	P _D	T _C = 25 °C	74	W		
Maximum power dissipation		T _C = 100 °C	29	٧V		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		

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ELECTRICAL SPECIFICATIONS PER LEG (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
		I _F = 15 A		-	1.3	1.7	v
Maximum forward voltage	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 0	-	1.0	10	
leakage current		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	400	1000	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8	-	nH

DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
D	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	19	-		
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 200 V	-	42	60	A A A A	
	t _{rr2}	T _J = 125 °C		-	70	120		
Peak recovery current	Peak recovery current I _{RRM1} T _J = 25 °C	T _J = 25 °C		-	4.0	6.0		
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	80	180		
See fig. 7	Q _{rr2}	T _J = 125 °C		-	220	600		
Peak rate of fall of	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-		
recovery current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A∕µs	

THERMAL - MECHANICAL SPECIFICATIONS PER LEG							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Junction to case, single leg conducting	Р				1.7		
Junction to case, both legs conducting	— R _{thJC}		-	-	0.85	K/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	r.∕ vv	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-		
Maight			-	6.0	-	g	
Weight			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		HFA301	A60CH		

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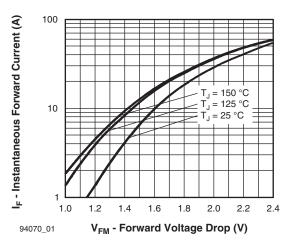
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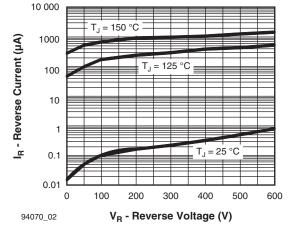
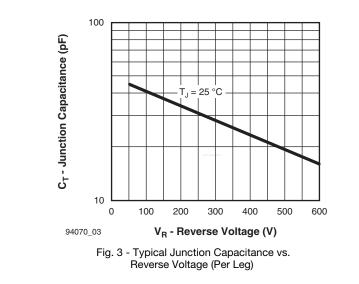
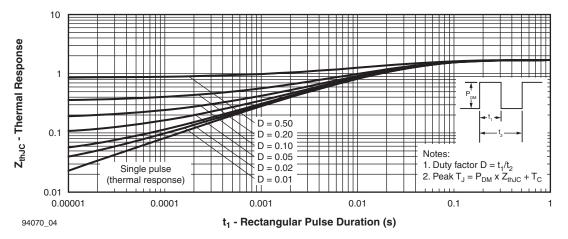


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)







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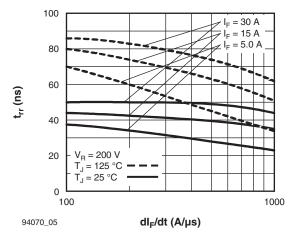


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

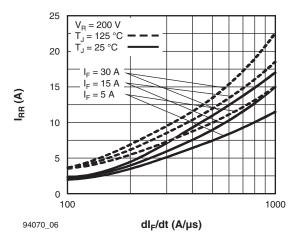


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

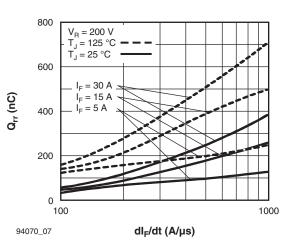


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

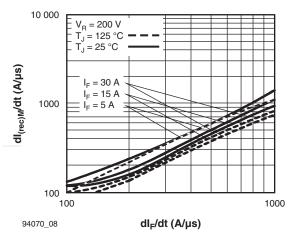


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

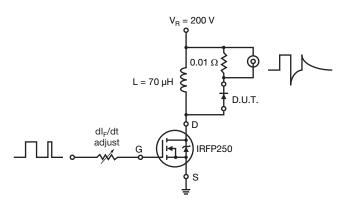


Fig. 9 - Reverse Recovery Parameter Test Circuit

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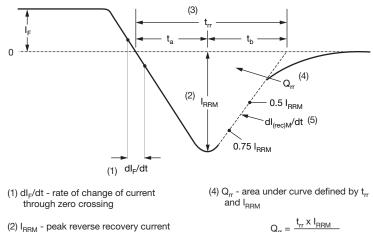
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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) dI_{(rec)M}/dt - peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	30	ТА	60	С	н	N3
	1	2	3	4	5	6	7	8	9
	 Vishay Semiconductors product 								
	2 -	2 - HEXFRED [®] family							
	3 -	3 - Electron irradiated							
	4 -	4 - Current rating (30 = 30 A)							
	5 -	5 - Package: TA = TO-220AB							
	6 -	- Voltage rating (60 = 600 V)							
	7 -								
	8 -	B - H = AEC-Q101 qualified							
	9 -								

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-HFA30TA60CHN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95222		
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028		

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